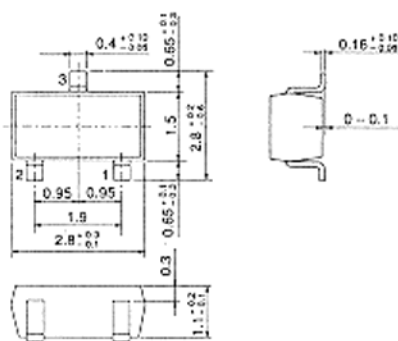


2SC2619

SILICON NPN EPITAXIAL
HIGH FREQUENCY AMPLIFIER



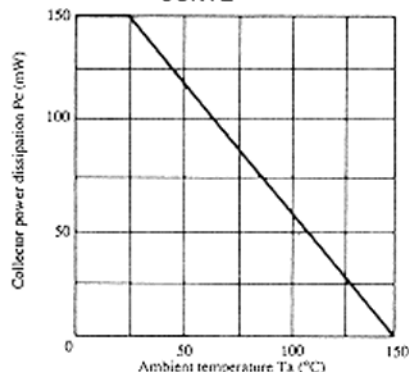
(MPAK)

1. Emitter.
 2. Base
 3. Collector
- (Dimensions in mm)

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SC2619	Unit
Collector to base voltage	V _{CB0}	30	V
Collector to emitter voltage	V _{CE0}	30	V
Emitter to base voltage	V _{EB0}	5	V
Collector current	I _C	100	mA
Collector power dissipation	P _C	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = 10μA, I _E = 0	30	—	—	V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = 1mA, R _{BE} = ∞	30	—	—	V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = 10μA, I _C = 0	5	—	—	V
Collector cutoff current	I _{CB0}	V _{CB} = 20V, I _E = 0	—	—	0.5	μA
Emitter cutoff current	I _{EB0}	V _{EB} = 2V, I _C = 0	—	—	0.5	μA
DC current transfer ratio	h _{FE} *	V _{CE} = 12V, I _C = 2mA	35	—	200	
Collector to emitter saturation voltage	V _{CE(sat)}	I _C = 10mA, I _B = 1mA	—	—	1.1	V
Base to emitter voltage	V _{BE}	V _{CE} = 12V, I _C = 2mA	—	—	0.75	V
Gain bandwidth product	f _T	V _{CE} = 12V, I _C = 2mA	—	230	—	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f = 1MHz	—	—	3.5	pF
Noise figure	NF	V _{CE} = 6V, I _C = 2mA, f = 1MHz, R _p = 500Ω	—	5.0	—	dB

* The 2SC2619 is grouped by h_{FE} as follows.

Grade	A	B	C
Mark	FA	FB	FC
h _{FE}	35 to 75	60 to 120	100 to 200

■ See characteristic curves of 2SC460.